

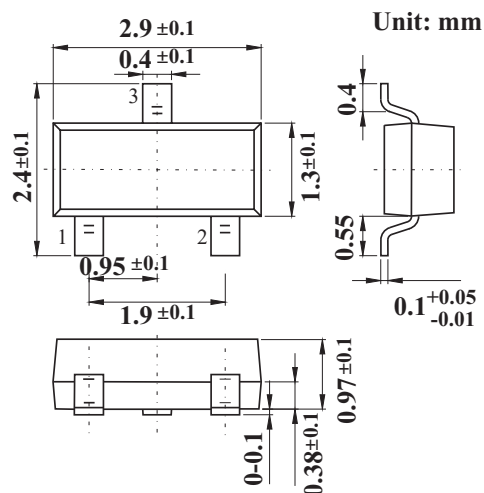
SOT-23 Plastic-Encapsulate Transistors

Features

- High breakdown voltage
- PNP Transistors

MECHANICAL DATA

- Case style: SOT-23 -3molded plastic
- Mounting position: any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	-55	V
Collector-emitter voltage	V_{CEO}	-50	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-150	mA
Collector dissipation	P_C	200	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-50 to 150	°C

PACKAGE INFORMATION

Device	Package	Shipping
2SA1179	SOT-23	3000/Tape&Reel

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CB0}	$I_C = -100\mu A, I_E = 0A$	-55			V
Collector-emitter breakdown voltage	V_{CEO}	$I_C = -1mA, I_B = 0A$	-50			V
Emitter-base breakdown voltage	V_{EBO}	$I_E = -100\mu A, I_C = 0A$	-5			V
Collector cutoff current	I_{CBO}	$V_{CB} = -35V, I_E = 0A$			-0.1	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = -4V, I_C = 0$			-0.1	μA
DC current Gain	h_{FE}	$V_{CE} = -6V, I_C = -1mA$	200		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -50mA, I_B = -5mA$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -50mA, I_B = -5mA$			-1.0	V
Output capacitance	C_{ob}	$V_{CB} = -6V, I_E = 0, f = 1MHz$		4.0		pF
Transition frequency	f_T	$V_{CE} = -6V, I_C = -10mA$		180		MHz

■ Marking

Marking	M
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RATINGS AND CHARACTERISTIC CURVES

